

Jordan D Greenlee

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Structural, Optical, and Electrical Characterization of Monoclinic $\hat{\Gamma}^2$ -Ga ₂ O ₃ Grown by MOVPE on Sapphire Substrates. <i>Journal of Electronic Materials</i> , 2016, 45, 2031-2037.	1.0	111
2	Substrate-Dependent Effects on the Response of AlGa _N /Ga _N HEMTs to 2-MeV Proton Irradiation. <i>IEEE Electron Device Letters</i> , 2014, 35, 826-828.	2.2	78
3	Symmetric Multicycle Rapid Thermal Annealing: Enhanced Activation of Implanted Dopants in Ga _N . <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P382-P386.	0.9	45
4	Selective p-type Doping of Ga _N :Si by Mg Ion Implantation and Multicycle Rapid Thermal Annealing. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, P124-P127.	0.9	43
5	Multicycle rapid thermal annealing optimization of Mg-implanted Ga _N : Evolution of surface, optical, and structural properties. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	39
6	Observation and control of the surface kinetics of InGa _N for the elimination of phase separation. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	38
7	Improved Vertical Ga _N Schottky Diodes with Ion Implanted Junction Termination Extension. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, Q176-Q178.	0.9	35
8	Impact of Surface Passivation on the Dynamic ON-Resistance of Proton-Irradiated AlGa _N /Ga _N HEMTs. <i>IEEE Electron Device Letters</i> , 2016, 37, 545-548.	2.2	33
9	Degradation mechanisms of 2-MeV proton irradiated AlGa _N /Ga _N HEMTs. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	32
10	Characterization of an Mg-implanted Ga _N p-n diode. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 2772-2775.	0.8	32
11	<i>In-situ</i> oxygen x-ray absorption spectroscopy investigation of the resistance modulation mechanism in LiNbO ₂ memristors. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	31
12	Proton Radiation-Induced Void Formation in Ni/Au-Gated AlGa _N /Ga _N HEMTs. <i>IEEE Electron Device Letters</i> , 2014, 35, 1194-1196.	2.2	30
13	Improvements in the Annealing of Mg Ion Implanted Ga _N and Related Devices. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2016, 29, 343-348.	1.4	30
14	Comparison of Interfacial and Bulk Ionic Motion in Analog Memristors. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 427-432.	1.6	28
15	Ultraviolet detector based on graphene/SiC heterojunction. <i>Applied Physics Express</i> , 2015, 8, 041301.	1.1	28
16	Halide based MBE of crystalline metals and oxides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 155-160.	0.8	20
17	Spatial Mapping of Pristine and Irradiated AlGa _N /Ga _N HEMTs With UV Single-Photon Absorption Single-Event Transient Technique. <i>IEEE Transactions on Nuclear Science</i> , 2016, 63, 1995-2001.	1.2	20
18	<i>In situ</i> investigation of the channel conductance of a Li ^x CoO ₂ (0 < x < 0.5) ionic-electronic transistor. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	18

#	ARTICLE	IF	CITATIONS
19	Radiation Effects on LiNbO ₃ Memristors for Neuromorphic Computing Applications. IEEE Transactions on Nuclear Science, 2013, 60, 4555-4562.	1.2	15
20	Characterization of a selective AlN wet etchant. Applied Physics Express, 2015, 8, 036501.	1.1	15
21	Liquid Phase Electro-Epitaxy of Memristive LiNbO ₃ Crystals. Crystal Growth and Design, 2014, 14, 2218-2222.	1.4	13
22	Comparison of AlN Encapsulants for Bulk GaN Multicycle Rapid Thermal Annealing. ECS Journal of Solid State Science and Technology, 2015, 4, P403-P407.	0.9	12
23	Defect reduction in MBE-grown AlN by multicycle rapid thermal annealing. Electronic Materials Letters, 2016, 12, 133-138.	1.0	12
24	Hyperspectral Electroluminescence Characterization of OFF-State Device Characteristics in Proton Irradiated High Voltage AlGaIn/GaN HEMTs. ECS Journal of Solid State Science and Technology, 2016, 5, Q289-Q293.	0.9	11
25	Comparison of AlN encapsulants for high-temperature GaN annealing. Applied Physics Express, 2014, 7, 121003.	1.1	10
26	Degradation mechanisms of AlGaIn/GaN HEMTs on sapphire, Si, and SiC substrates under proton irradiation. , 2014, , .		9
27	Thermal etching of nanocrystalline diamond films. Diamond and Related Materials, 2015, 59, 116-121.	1.8	9
28	Spatiotemporal drift-diffusion simulations of analog ionic memristors. Journal of Applied Physics, 2013, 114, .	1.1	8
29	Molecular beam epitaxy growth of niobium oxides by solid/liquid state oxygen source and lithium assisted metal-halide chemistry. Journal of Crystal Growth, 2015, 425, 225-229.	0.7	8
30	Temporary Bonding with Polydimethylglutarimide Based Lift Off Resist as a Layer Transfer Platform. ECS Journal of Solid State Science and Technology, 2015, 4, P190-P194.	0.9	7
31	UV Single-Photon Absorption Single-Event Transient Testing of Pristine and Irradiated AlGaIn/GaN HEMTs. , 2015, , .		3
32	In situ Auger probe enabling epitaxy composition control of alloys by elemental surface analysis. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 03C126.	0.6	2
33	Process optimization of multicycle rapid thermal annealing of Mg-implanted GaN. , 2014, , .		1
34	Elimination of Basal Plane Dislocations in Epitaxial 4H-SiC via Multicycle Rapid Thermal Annealing. Materials Science Forum, 2015, 821-823, 297-302.	0.3	1